

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI MRF427** is Designed for high voltage applications up to 30 MHz

**FEATURES:**

- $P_G = 18$  dB min. at 25 W/30 MHz
- $IMD_3 = -34$  dBc max. at 25 W<sub>(PEP)</sub>
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	6.0 A
$V_{CBO}$	110 V
$V_{CEO}$	65 V
$V_{EBO}$	4.0 V
$P_{DISS}$	80 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	2.19 $^\circ C/W$

**PACKAGE STYLE .500 4L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

**ORDER CODE: ASI10467**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 100$ mA	110			V
$BV_{CES}$	$I_C = 100$ mA	110			V
$BV_{CEO}$	$I_C = 200$ mA	65			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		90	---
$C_{ob}$	$V_{CB} = 50$ V $f = 1.0$ MHz			60	pF
$G_P$ $IMD_3$	$V_{CE} = 50$ V $P_{OUT} = 25$ W (PEP) $f = 30$ MHz	18	20 - 37	-34	dB dBc